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LIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)

| Attorney Docket Number: 5308-157IP2 | Serial No.: 10/045,542 |
|---|---|
| Applicants: Das et al. | |
| Filing Date: October 26, 2001 | Group: 1762 |







U. S. PATENT DOCUMENTS

| Examiner Initial | | Document Number | Date | Name | Class | Subclass | Filing Date if Appropriate |
|---|---|---|---|---|---|---|---|
| | 1 | 5,170,231 | 12/8/92 | Fujii et al. | 357 | 23.2 | |
| | 2 | 5,972,801 | 10/26/99 | Lipkin et al. | 438 | 770 | |
| | 3 | 6,165,822 | 12/26/00 | Okuno et al. | 438 | 142 | |
| | 4 | 6,221,700 | 4/24/01 | Okuno et al. | 438 | 151 | |
| | 5 | 6,455,892 | 9/24/02 | Okuno et al. | 257 | 328 | |
| | 6 | 2002/0072247A1 | 6/13/02 | Lipkin et al. | 438 | 767 | |

FOREIGN PATENT DOCUMENTS

| | | Document Number | Date | Country | Class | Subclass | Translation |
|---|---|---|---|---|---|---|---|
| | 7 | JP02000252461A | 9/14/00 | Japan | — | — | Abstract |

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|---|---|---|
| | 8 | Copy of International Search Report for PCT/US02/11691. |
| | 9 | Xu et al. "Improved Performance and Reliability of $N_2O$-Grown Oxynitride on 6H-SiH," *IEEE Electron Device Letters*. Vol. 21, No.6, June 2000, p. 298-300. |
| | 10 | Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," *IEEE Transactions on Electron Devices*. Vol. 47, No. 2, February 2000, pp. 458-462. |
| | 11 | Lai et al. "Interface Properties of $N_2O$-Annealed $NH_3$-Treated 6H-SiC MOS Capacitor," *Electron Devices Meeting*, June 26, 1999, pp. 46-9. |
| | 12 | Lipkin et al. "Challenges and State-of-the-Art of Oxides on SiC," *Mat. Res. Symp. Proc.* Vol. 640, 2001. |
| | 13 | Cho et al. "Improvement of charge trapping by hydrogen post-oxidation annealing in gate oxide of 4H-SiC methel-oxide-semiconductor capacitors," *Applied Physics Letters*. Vol. 77, No. 8, pp. 1215-7, 8/2 000 |
| | 14 | Fukuda et al. "Improvement of $SiO_2$/4H-SiC Interface Using High-Temperature Hydrogen Annealing at Low Pressure and Vacuum Annealing," *Jpn J. Appl. Phys.* Vol. 38, April 1999, pp. 2306-9 |
| | 15 | Suzuki et al. "Effect of Post-oxidation-annealing in Hydrogen on $SiO_2$/4H-SiC Interface," *Materials Science Forum*, Vols. 338-342 (2000) 1073-6. |
| | 16 | Leonhard et al. "Long term stability of gate-oxides on n- and p-type silicon carbide studied by charge injection techniques," *Materials Science Engineering*, Vol. 46, No. 1-3, April 1997, pp. 263-6. |
| | 17 | Fukuda et al. "Improvement of $SiO_2$/4H-SiC Interface by Using High Temperature Hydrogen Annealing at 1000° C," *Extended Abstracts of the International Conference on Solid State Devices and Materials,"* Japan Society of Applied Physics, Tokyo, Japan, Sept. 1998. |
| | 18 | Chang et al. "Observation of a Non-stoichiometric Layer at the Silicon Dioxide--Silicon Carbide Interface: Effect of Oxidation Temperature and Post-Oxidation Processing Conditions," *Mat. Res. Soc. Symp. Proc.* Vol. 640, 2001. |